

REMARKS

By the foregoing amendments to the specification, a cross-reference to the parent international application has been provided and obvious typographical errors have been corrected. The claims have been amended to better conform to U.S. practice and to omit multiple dependencies. New claims 26-31 find support in original claims 5-10.

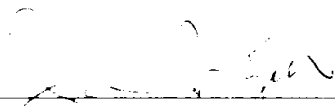
The filing fee has been calculated based on the claims as amended above. No new matter has been added.

Respectfully submitted,

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August 13, 2001

By


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VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE SPECIFICATION:

Paragraph beginning at page 5, line 1 has been amended as follows:

The work function of the material of the third layer is preferably greater than 4.0 eV. The higher work function material is suitably a metal or an oxide. The higher work function material and/or the third layer itself preferably has an electrical conductivity greater than $10^5 [(*.cm)^{-1}] (\Omega.cm)^{-1}$. The higher work function material is preferably Al, Cu, Ag, Au or Pt; or an alloy of two or more of those metals; or an alloy of one or more of those metals together with another metal; or an oxide such as tin oxide or indium-tin oxide (ITO). The thickness of the third layer is preferably in the range from 1000 Å to 10000 Å, preferably in the range from 2000 Å to 6000 Å, and most preferably around 4000 Å.

Please insert a new paragraph beginning at page 7, following line 5 as follows:

--figure 1 shows a typical cross-sectional structure of a prior art organic light-emissive device;--

Paragraph beginning at page 7, line 28 has been amended as follows:

To form the device of figure 2 a transparent layer of ITO to form the anode electrode 10 may first be deposited on a sheet of glass 14. The glass sheet could be a sheet of sodalime or borosilicate glass of a thickness of, for instance, 1mm. The thickness of the ITO coating is suitably around 100 to 150nm and the ITO suitably has a resistance of between 10 and 30 [$\frac{*}{\square}$] Ω/\square . ITO-coated glass substrates of this type

are commercially available. As an alternative to glass, the sheet 14 could be formed of perspex. As an alternative to ITO, gold or TO could be used as the anode.

Paragraph beginning at page 13, line 26 has been amended as follows:

[The applicant draws attention to the fact that the present] The invention may include any inventive feature or combination of features disclosed herein either implicitly or explicitly or any generalisation thereof, without limitation to the scope of any of the [present] claims. In view of the foregoing description it will be evident to a person skilled in the art that various modifications may be made within the scope of the invention.

IN THE CLAIMS:

Please amend claims 4, 5, 7-19, and 22 as follows:

4. (Amended) An opto-electrical device as claimed in [any preceding] claim 1, wherein the compound is a fluoride.

5. (Amended) An [opti-electrical] opto-electrical device as claimed in [any of claims] claim 2 [to 4], wherein the metal is a group 1 or 2 metal.

7. (Amended) An opto-electrical device as claimed in [any of claims] claim 2 [to 6], wherein the said one of the layers is the first layer.

8. (Amended) An opto-electrical device as claimed in [any of claims] claim 2 [to 6], wherein the said one of the layers is the second layer.

9. (Amended) An opto-electrical device as claimed in [any of claims] claim 2 [to 8], wherein the other of the first and second layers comprises a metal.

10. (Amended) An opto-electrical device as claimed in claim 9, wherein the other of the first and second layers comprises a metal selected from the group [comprising:] consisting of Li, Ba, Mg, Ca, Ce, Cs, Eu, Rb, K, Y, Sm, Na, Sm, Sr, Tb [or] and Yb.

11. (Amended) An opto-electrical device as claimed in [any preceding] claim 1, wherein the second layer is thicker than the first layer.

12. (Amended) An opto-electrical device as claimed in [any preceding] claim 1, wherein the thickness of the second layer is greater than 100 Å.

13. (Amended) An opto-electrical device as claimed in [any preceding] claim 1, wherein the said material having a work function below 3.5 eV of which the first layer is comprised has a higher work function than the said material having a work function below 3.5 eV of which the second layer is comprised.

14. (Amended) An opto-electrical device as claimed in [any preceding] claim 1, wherein the thickness of the third layer is greater than 1000 Å.

15. (Amended) An opto-electrical device as claimed in [any preceding] claim 1, wherein the said material having a work function above 3.5 eV has an electrical conductivity greater than $10^5 [(\text{*.cm})^{-1}] (\text{Q.cm})^{-1}$.

16. (Amended) An opto-electrical device as claimed in [any preceding] claim 1, wherein the said material having a work function above 3.5 eV is aluminium, gold or indium-tin oxide.

17. (Amended) An opto-electrical device as claimed in [any preceding] claim 1, wherein the cathode is transparent.

18. (Amended) An opto-electrical device as claimed in [any preceding] claim 1, wherein the opto-electrically active region is light-emissive.

19. (Amended) An opto-electrical device as claimed in [any preceding] claim 1, wherein the opto-electrically active region comprises a light-emissive organic material.

22. (Amended) An opto-electrical device as claimed in [any of claims] claim 19 [to 21], comprising a charge transport layer between the light-emissive organic material and one of the electrodes.

Please delete claims 24 and 25, without prejudice.

Please add new claims 26-31, as follows:

26. An opto-electrical device as claimed in claim 4, wherein the metal is a group 1 or 2 metal.
27. An opto-electrical device as claimed in claim 26, wherein the metal is lithium.
28. An opto-electrical device as claimed in claim 4, wherein the said one of the layers is the first layer.
29. An opto-electrical device as claimed in claim 4, wherein the said one of the layers is the second layer.
30. An opto-electrical device as claimed in claim 4, wherein the other of the first and second layers comprises a metal.
31. An opto-electrical device as claimed in claim 30, wherein the other of the first and second layers comprises a metal selected from the group consisting of Li, Ba, Mg, Ca, Ce, Cs, Eu, Rb, K, Y, Sm, Na, Sm, Sr, Tb and Yb.